

Dual Driver Transistors

NPN/PNP Duals

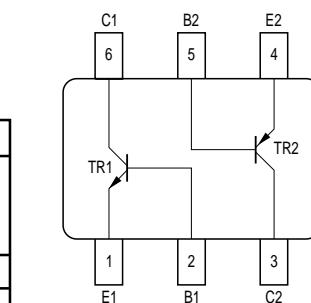
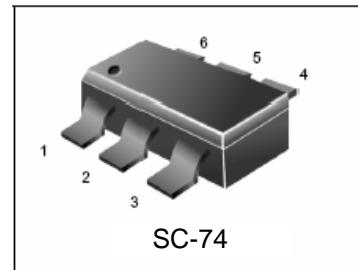
LMBTA05UT1G
LMBTA06UT1G

FEATURES

- We declare that the material of product compliance with RoHS requirements.

MAXIMUM RATINGS

Rating	Symbol	LMBTA05	LMBTA06	Unit
Collector-Emitter Voltage	V_{CEO}	60	80	Vdc
Collector-Base Voltage	V_{CBO}	60	80	Vdc
Emitter-Base Voltage	V_{EBO}	4.0		Vdc
Collector Current — Continuous	I_C	500		mAdc



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (1)	P_D	225	mW
$T_A = 25^\circ\text{C}$		1.8	$\text{mW}/^\circ\text{C}$
Derate above 25°C			
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation	P_D	300	mW
Alumina Substrate, (2) $T_A = 25^\circ\text{C}$		2.4	$\text{mW}/^\circ\text{C}$
Derate above 25°C			
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

DEVICE MARKING

LMBTA05UT1G = 3H, LMBTA06UT1G = 3GM;

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage(3) ($I_C = 1.0 \text{ mA}, I_B = 0$)	$V_{(BR)CEO}$	60	—	Vdc
	LMBTA05	80	—	
Emitter-Base Breakdown Voltage ($I_E = 100 \mu\text{A}, I_C = 0$)	$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 60\text{Vdc}, I_B = 0$)	I_{CES}	—	0.1	μAdc
Emitter Cutoff Current ($V_{CB} = 60\text{Vdc}, I_E = 0$)	I_{CBO}	—	0.1	μAdc
	LMBTA05	—	0.1	
	LMBTA06	—	0.1	

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

3. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

LMBTA05UT1G LMBTA06UT1G
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS				
DC Current Gain ($I_C = 10 \text{ mA}_\text{dc}$, $V_{CE} = 1.0 \text{ V}_\text{dc}$)	h_{FE}	100	—	—
($I_C = 100 \text{ mA}_\text{dc}$, $V_{CE} = 1.0 \text{ V}_\text{dc}$)		100	—	—
Collector-Emitter Saturation Voltage ($I_C = 100 \text{ mA}_\text{dc}$, $I_B = 10 \text{ mA}_\text{dc}$)	$V_{CE(\text{sat})}$	—	0.25	V_dc
Base-Emitter On Voltage ($I_C = 100 \text{ mA}_\text{dc}$, $V_{CE} = 1.0 \text{ V}_\text{dc}$)	$V_{BE(\text{sat})}$	—	1.2	V_dc

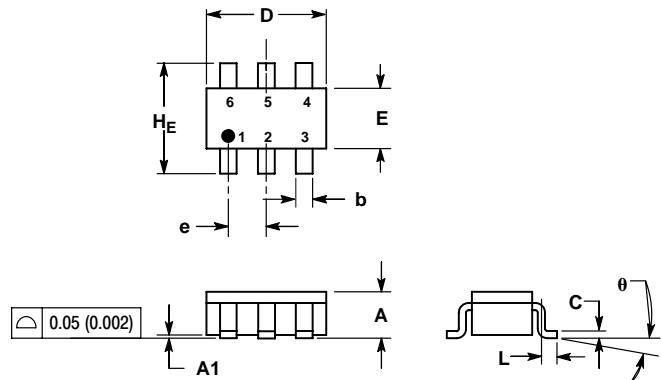
SMALL-SIGNAL CHARACTERISTICS

Current-Gain - Bandwidth Product(4) ($V_{CE} = 2.0 \text{ V}$, $I_C = 10 \text{ mA}$, $f = 100 \text{ MHz}$)	f_T	100	—	MHz
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4. f_T is defined as the frequency at which $|h f_e|$ extrapolates to unity.

ORDERING INFORMATION

Device	Marking	Shipping
LMBTA05UT1G	3H	3000/Tape & Reel
LMBTA06UT1G	3GM	3000/Tape & Reel

LMBTA05UT1G LMBTA06UT1G
SC-74


DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
H_E	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	-	10°	0°	-	10°

